

Silicon PNP Power Transistors

2SB1017

DESCRIPTION

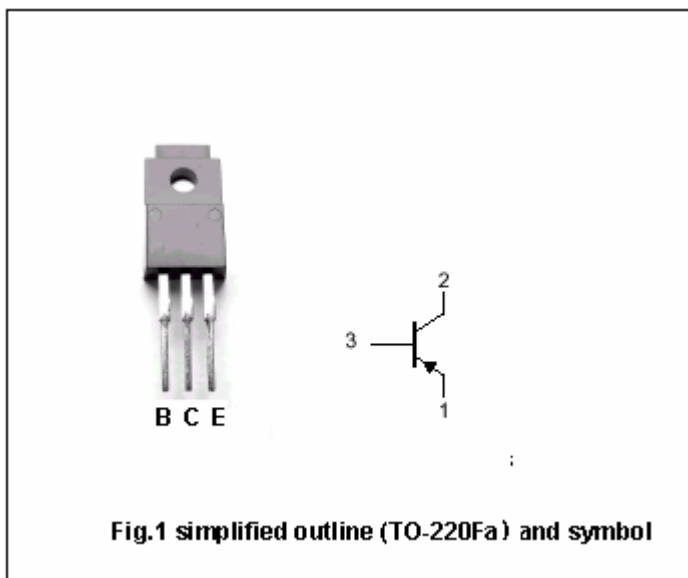
- With TO-220Fa package
- Complement to type 2SD1408

APPLICATIONS

- For power amplifications
- Recommended for 20-25W high-fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-4	A
I _B	Base current		-0.4	A
P _C	Collector power dissipation	T _a =25°C	2.0	W
		T _C =25°C	25	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; I _B =0	-80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A		-1.0	-1.7	V
V _{BE}	Base-emitter on voltage	I _C =-3A; V _{CE} =-5V		-1.0	-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V; I _E =0			-30	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-5V	40		240	
h _{FE-2}	DC current gain	I _C =-3A; V _{CE} =-5V	15			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-5V		9		MHz
C _{OB}	Collector output capacitance	I _E =0, f=1MHz; V _{CB} =-10V		130		pF

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

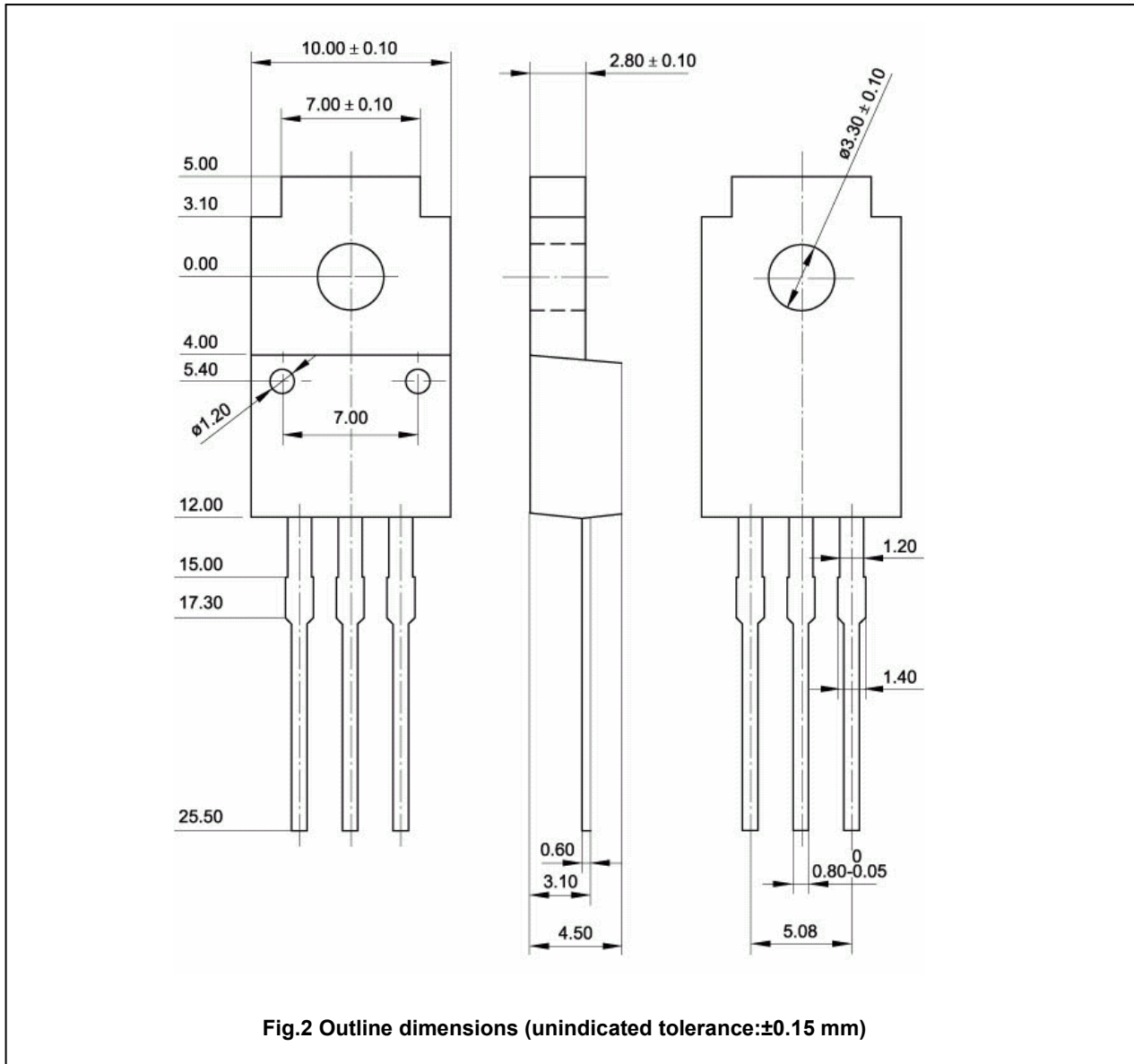


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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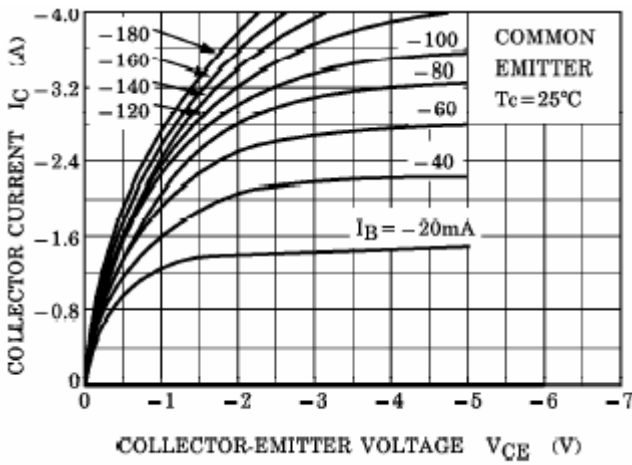


Fig.3 Static Characteristic

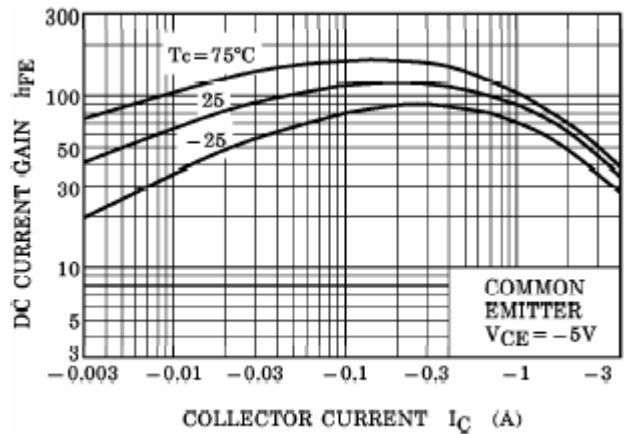


Fig.4 DC current Gain

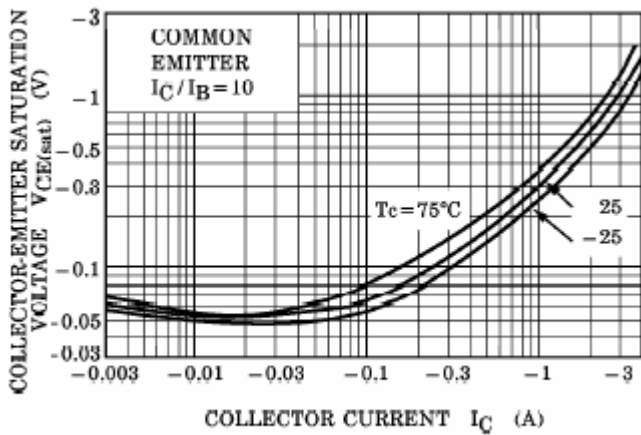


Fig.5 Collector-Emitter Saturation Voltage

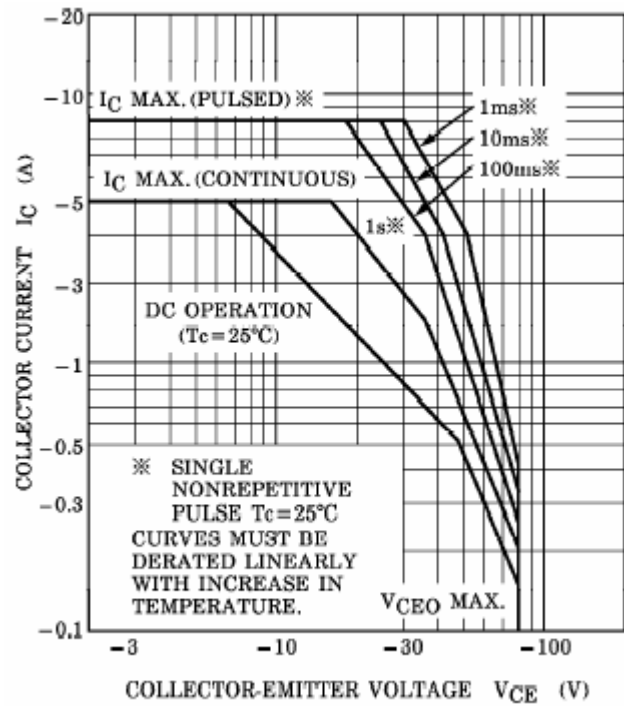


Fig.6 Safe Operating Area